INC5002AP1

For low frequency power amplify Silicon NPN Epitaxial

DESCRIPTION

INC5002AP1 is a silicon NPN epitaxial transistor designed for relay drive or Power supply application.

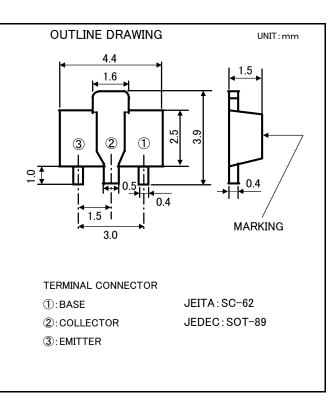
FEATURE

•Small package for easy mounting.

- ●High voltage VCEO=60V
- •High collector current Ic=3A
- ●Low VCE(sat) VCE(sat)=0.6V max(@Ic=3A/ IB=300mA)
- ●High collector dissipation Pc=500mW

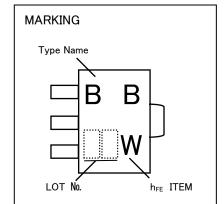
APPLICATION

DC·DC converter, Relay drive, Motor drive



MAXIMUM RATING(Ta=25°C)

| SYMBOL | PARAMETER | RATING | UNIT | |
|------------------|--------------------------------|----------|------|--|
| V _{CBO} | Collector to Base voltage | 80 | V | |
| V _{EBO} | Emitter to Base voltage | 6 | V | |
| V _{CEO} | Collector to Emitter voltage | 60 | V | |
| Ic | Collector current | 3 | A | |
| I _{CM} | Peak Collector current | 6 | | |
| Pc | Collector dissipation(Ta=25°C) | 500 | mW | |
| Tj | Junction temperature | +150 | °C | |
| T_{stg} | Storage temperature | -55~+150 | °C | |



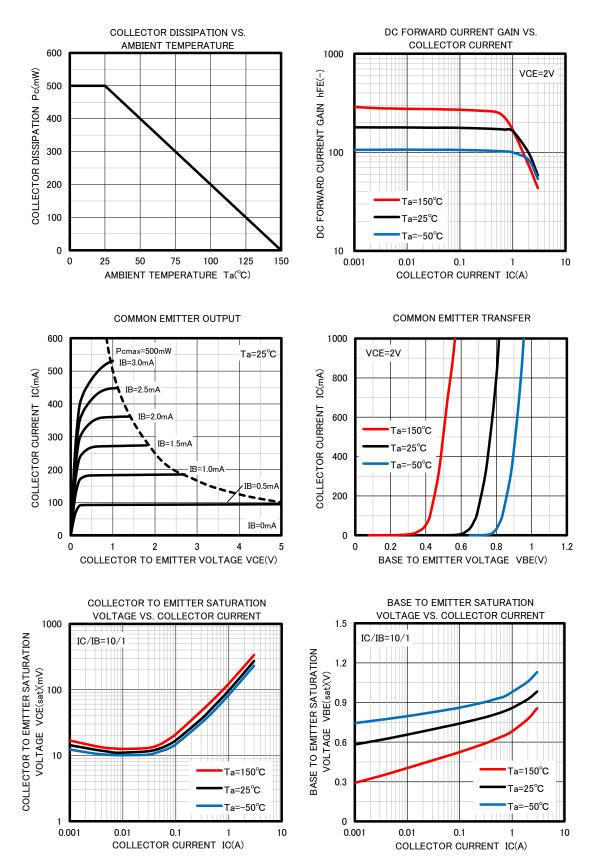
ELECTRICAL CHARACTERISTICS (Ta=25°C)

| SYMBOL | PARAMETER | | LIMITS | | | UNIT |
|-----------------------------|------------------------------|--|--------|-----|-----|------|
| | | TEST CONDITIONS | | TYP | MAX | UNIT |
| V _{(BR)CBO} | C to B breakdown voltage | $I_c=100 \mu A$, $I_E=0mA$ | 80 | - | - | ٧ |
| $V_{(BR)EBO}$ | E to B breakdown voltage | I_{E} =100 μ A, I_{C} =0mA | 6 | - | - | ٧ |
| V _{(BR)CEO} | C to E breakdown voltage | I _C =1mA, R _{BE} =∞ | 60 | - | - | V |
| I _{CBO} | Collector cut off current | V _{CB} =60V, I _E =0mA | - | - | 1.0 | μA |
| Iево | Emitter cut off current | V _{EB} =4V, Ic=0mA | - | - | 1.0 | μA |
| hfe | DC forward current gain | Vce=2V, Ic=0.5A | 100 | - | 300 | - |
| $V_{\text{CE}(\text{sat})}$ | C to E saturation voltage | Ic=3A, I _B =300mA | - | - | 0.6 | ٧ |
| fr | Gain band width product | Vce=5V, Ie=-100mA | - | 200 | - | MHz |
| Cob | Collector output capacitance | V_{CB} =10V, I _E =0mA, f=1MHz | - | 15 | - | pF |

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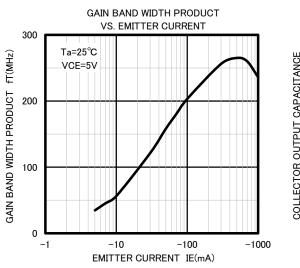
TYPICIAL CHARACTERISTICS

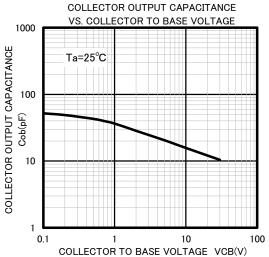


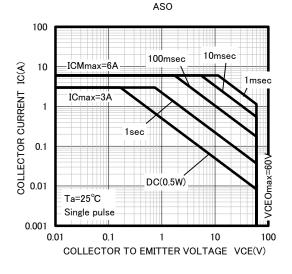
ISAHAYA ELECTRONICS CORPORATION

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